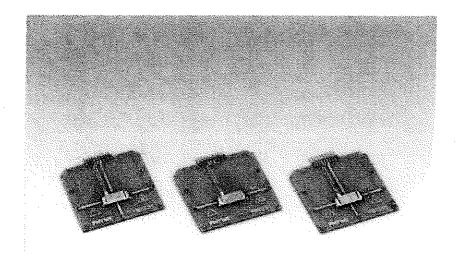


Hall effect,p-Ge,carrier board

Product No: 11805-01



Function and Application

In connection with Halleffect-module for determination of temperature dependent Hall voltage and conductivity of doped semiconductors.

Equipment and technical data

Heatable carrier board with p-Ge-crystal, Pt100-Thermocouple, integrated heating and 4-mm-connection

Dimensions of crystal (mm): 20 x 10 x 1. Spec. resistance: approx. 2.0 - 2.5 Ohm cm.

Max. crystal temperature: 170 °C. Max. probe current: +/- 60 mA.

Dimensions of circuit board (mm): 73 x 70 x 3.

Weight: 0.03 kg

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